



#### 40V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>A</sub> = +25°C
-40V	11mΩ @ V <sub>GS</sub> = -10V	-11A
-40V	15mΩ @ V <sub>GS</sub> = -4.5V	-10A

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC converters
- Power management functions
- Analog switches

#### **Features and Benefits**

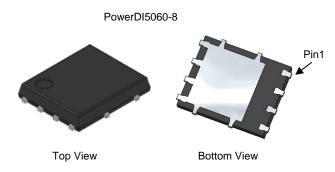
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES™ DMP4015SPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

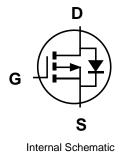
https://www.diodes.com/quality/product-definitions/

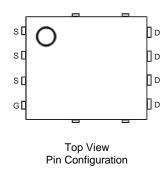
#### **Mechanical Data**

- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—100% Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

#### Site1:

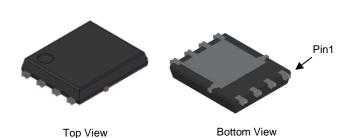


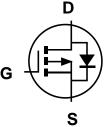




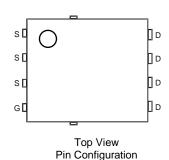
Site2:

PowerDI5060-8 (SWP) (Type UX)





Internal Schematic



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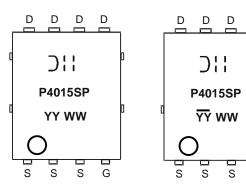
### Ordering Information (Note 4)

Part Number	Package	Packing		
Fait Nullibei	rackage	Qty.	Carrier	
DMP4015SPSQ-13	PowerDI5060-8	2,500	Reel	
DMP4015SPSQ-13	PowerDI5060-8 (SWP) (Type UX)	2,500	Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

#### **Marking Information**



Dill= Manufacturer's Marking
P4015SP = Product Type Marking Code
YYWW or YYWW = Date Code Marking
YY or YY= Year (ex: 22 = 2022)
WW = Week (01 to 53)

## **Maximum Ratings** (@TA = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-40	V
Gate-Source Voltage			Vgss	±25	V
Continuous Dusin Comment (Nata 5) \/ 40\/	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-8.5 -6.8	А
Continuous Drain Current (Note 5) V <sub>G</sub> S = -10V	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	lo	-13.0 -10.5	А
Continuous Prois Current (Note C) V 40V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	lo	-11.0 -8.7	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-17.0 -13.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-100	Α
Maximum Body Diode Continuous Current (Note 6)			Is	-11	Α
Avalanche Current L = 1mH			las	-22	Α
Avalanche Energy L = 1mH			Eas	242	mJ

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Dawar Dissination (Note 5)	T <sub>A</sub> = +25°C	D-	1.3	W
Total Power Dissipation (Note 5)	T <sub>A</sub> = +70°C	Pb	0.8	
Thermal Begistenes, Juneties to Ambient (Note 5)	Steady State	Davi	96.4	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t < 10s	Reja	40.6	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	Pn	2.1	W
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	PD	1.4	
Thermal Registeres Junction to Ambient (Note 6)	Steady State	D	49	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t < 10s	$R_{\theta JA}$	24	°C/W
Thermal Resistance, Junction to Case (Note 7)		R <sub>0</sub> JC	1.6	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.

- 6. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).



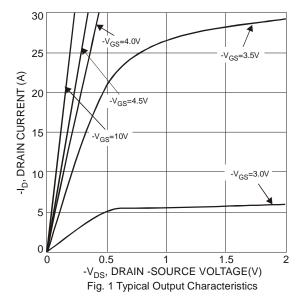
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

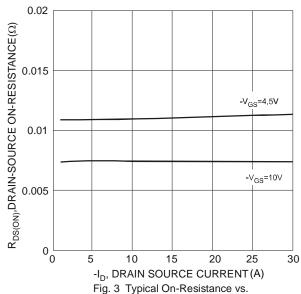
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BVDSS	-40	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	-1	μΑ	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	Vgs(TH)	-1.5	-2	-2.5	٧	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	
Static Drain-Source On-Resistance	Descour	-	7	11	mΩ	$V_{GS} = -10V, I_{D} = -9.8A$	
Static Dialii-Source Off-Resistance	RDS(ON)	_	9	15	11122	$V_{GS} = -4.5V, I_{D} = -9.8A$	
Forward Transfer Admittance	Y <sub>fs</sub>	_	26	_	S	$V_{DS} = -20V, I_{D} = -9.8A$	
Diode Forward Voltage	VsD		-0.7	-1	V	Vgs = 0V, Is = -1A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	-	4,234	_		V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V f = 1MHz	
Output Capacitance	Coss	_	1,036	_	pF		
Reverse Transfer Capacitance	Crss	_	526	_			
Gate Resistance	Rg	_	7.77	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	_	47.5	_		V 00V V 5V	
Gate-Source Charge	Qgs		14.2	_	nC	$V_{DS} = -20V, V_{GS} = -5V$ $I_{D} = -9.8A$	
Gate-Drain Charge	Qgd	_	13.5	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	13.2	_		$V_{GS} = -10V$ , $V_{DD} = -20V$ , $R_{G} = 6\Omega$ , $I_{D} = -1A$ , $R_{L} = 20\Omega$	
Turn-On Rise Time	tR	_	10	_			
Turn-Off Delay Time	tD(OFF)	-	302.7	_	ns		
Turn-Off Fall Time	tF	_	137.9	_			

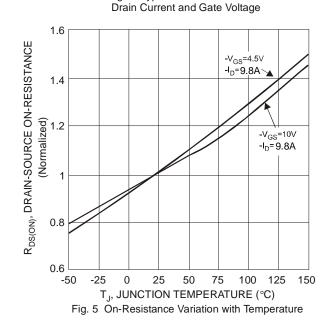
Notes: 8. Short duration pulse test used to minimize self-heating effect 9. Guaranteed by design. Not subject to production testing.

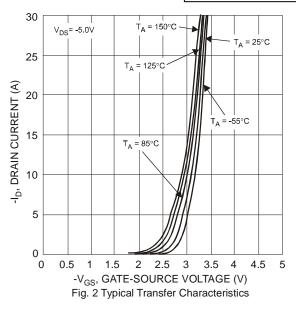












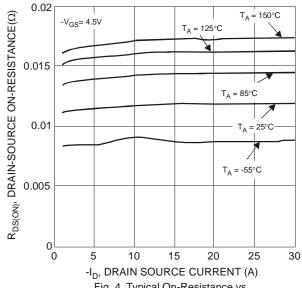


Fig. 4 Typical On-Resistance vs.
Drain Current and Temperature

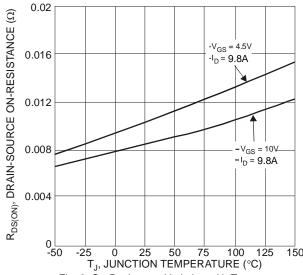


Fig. 6 On-Resistance Variation with Temperature



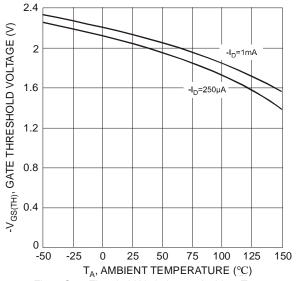
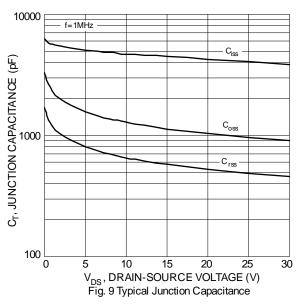
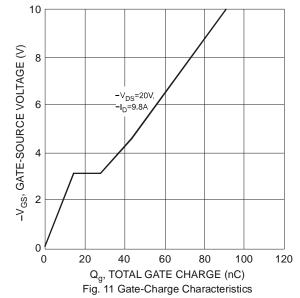
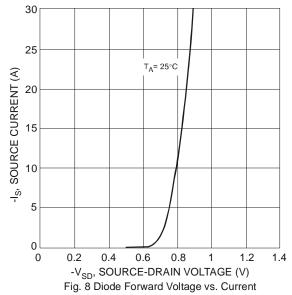


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







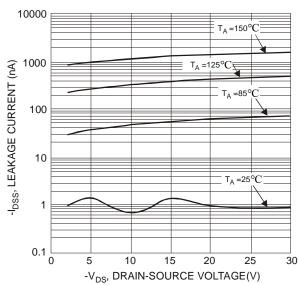


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

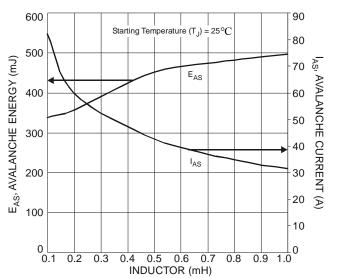
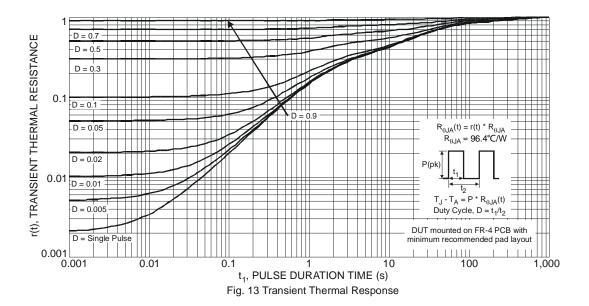


Fig. 12 Single-Pulse Avalanche Tested





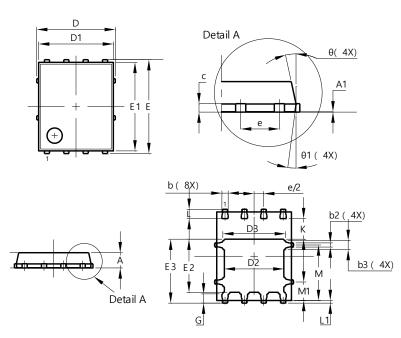


## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### Site1:

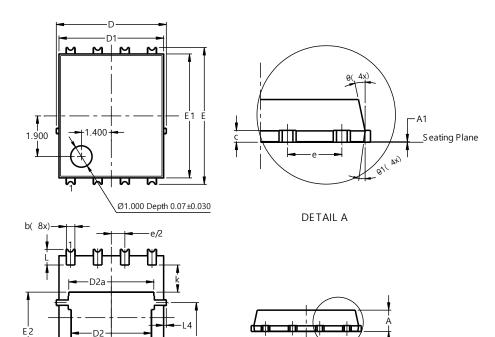
#### PowerDI5060-8



PowerDI5060-8			
Dim	Min	Max	Тур
Α	0.90	1.10	1.00
A1	0.00	0.05	_
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
С	0.230	0.330	0.277
D		5.15 BSC	;
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
Е	(	6.15 BSC	;
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e G	1.27 BSC		
	0.51	0.71	0.61
K	0.51	_	-
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
М	3.235	4.035	3.635
M1	1.00	1.40	1.21
Θ	10°	12°	11°
Θ1	6°	8°	7°
All Dimensions in mm			

Site2:

#### PowerDI5060-8 (SWP) (Type UX)



(Type UX)				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0	0.05		
b	0.30	0.50	0.41	
b2	0.20	0.35	0.25	
b4		).25REF	-	
С	0.230	0.330	0.277	
D	5	.15 BS0	)	
D1	4.70	5.10	4.90	
D2	3.56	3.96	3.76	
D2a	3.78	4.18	3.98	
E	6	.40 BS0	)	
E1	5.60	6.00	5.80	
E2	3.46	3.86	3.66	
E2a	4.195	4.595	4.395	
е		.27BSC	)	
k	1.05			
L	0.635	0.835	0.735	
La	0.635	0.835	0.735	
L1	0.200	0.400	0.300	
L1a	0.050REF			
L4	0.025	0.225	0.125	
M	3.205	4.005	3.605	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				

PowerDI5060-8 (SWP)

DETAIL A

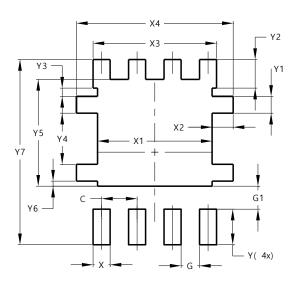


## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### Site1:

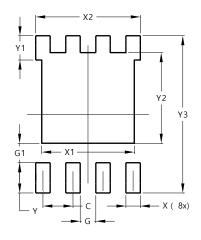
#### PowerDI5060-8



Dimensions	ions Value (in mm)	
С	1.270	
G	0.660	
G1	0.820	
Х	0.610	
X1	4.100	
X2	0.755	
Х3	4.420	
X4	5.610	
Y	1.270	
Y1	0.600	
Y2	1.020	
Y3	0.295	
Y4	1.825	
Y5	3.810	
Y6	0.180	
Y7	6.610	

#### Site2:

#### PowerDI5060-8 (SWP) (Type UX)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610



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